Electronic Supplementary Material (ESI) for Journal of Materials Chemistry C.

Supporting information

All Solution-Processed Hafnium Rich Hybrid Dielectrics for Hysteresis Free Metal-Oxide Thin-film Transistors

J. Meza Arroyo[a1], M.G. Syamala Rao[a1*], M.S. de Urquijo Ventura [a], V. H. Martínez-Landero[b], Trey B. Daunis [c], Ovidio Rodríguez [d], Julia W. P. Hsu [c], R. Ramírez Bon [a*]

[a]Centro de Investigación y de Estudios Avanzados del IPN, Unidad Querétaro, Apdo, Postal 1-798, 76001, Querétaro, Querétaro, México.

[b] Facultad de Metalurgia, Universidad Autónoma de Coahuila, Carr. 57, km. 5, C.P.25720, Monclova, Coahuila, México.

[c]Department of Materials Science and Engineering, The University of Texas at Dallas, 800 West Campbell Road, Richardson, Texas 75080, United States.

[d]Department of Electrical and Computer Engineering, The University of Texas at Dallas, 800 West Campbell Road, Richardson, Texas, 75080, United States.

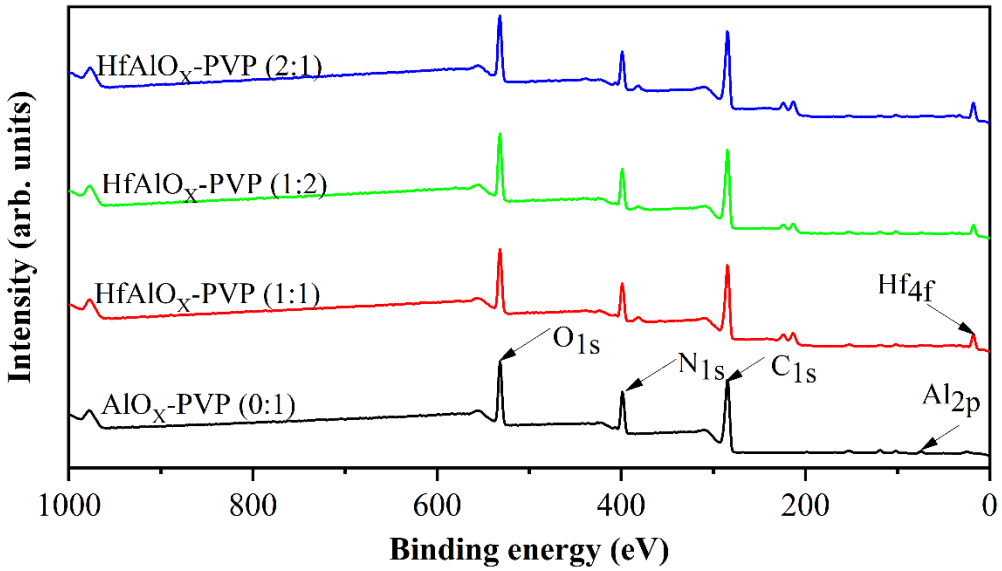

Fig.S1. XPS survey scan spectra of AlOx-PVP and HfAlOx-PVP hybrid thin films.

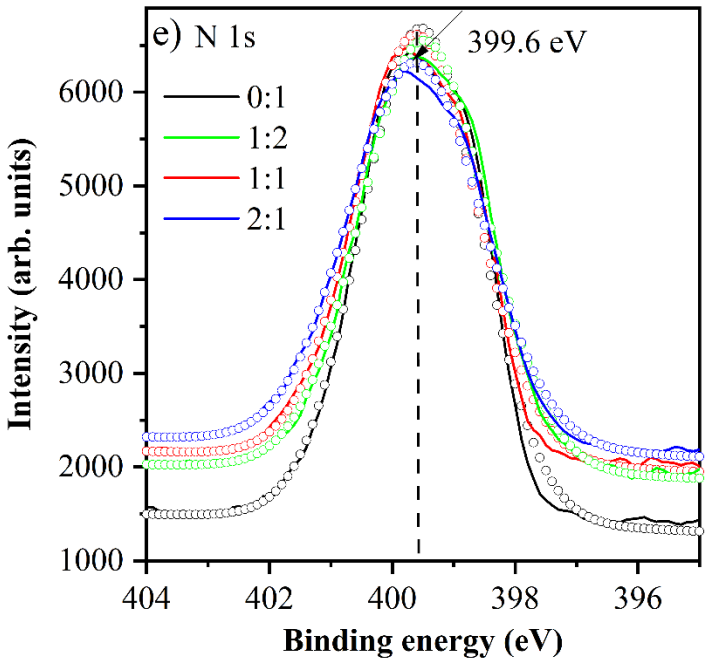

Fig.S2 XPS spectra of AlOx-PVP and HfAlOx-PVP hybrid thin films f) N 1s spectra.

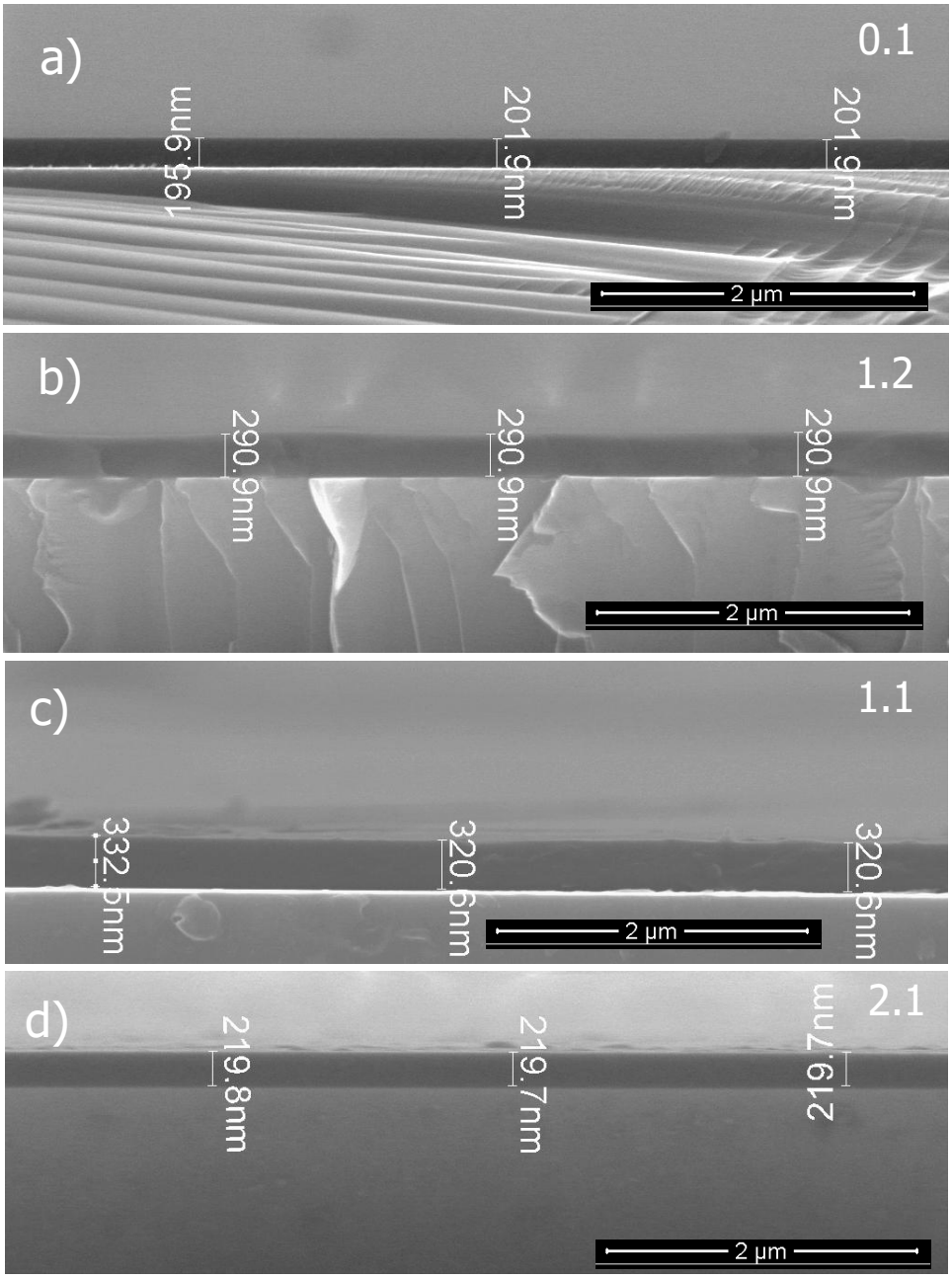

Fig.S3 FESEM cross section images of AlOx-PVP and HfAlOx-PVP hybrid dielectric thin films a) 0:1 b) 1:2 c) 1:1 and d) 2:1.